

SMT850N

High Performance Infrared TOP IR LED

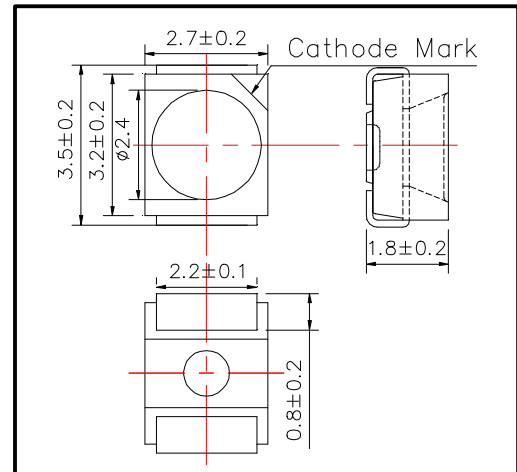
SMT850N consists of an AlGaAs LED mounted on the lead frame as TOP LED package and is 16mW typical of output power.

It emits a spectral band of radiation at 850nm.

Specifications

- 1) Product Name TOP IR LED
- 2) Type No. SMT850N
- 3) Chip
 - (1) Chip Material AlGaAs
 - (2) Peak Wavelength 850nm typ.
- 4) Package
 - (1) Lead Frame Die Silver Plated
 - (2) Package Resin PPA Resin
 - (3) Lens Epoxy Resin

Outer dimension(Unit:mm)



Absolute Maximum Rating

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	160	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	500	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-20 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +80	°C	
Soldering Temperature	T _{SOL}	240	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition : Soldering condition must be completed within 3 seconds at 260°C

Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA		1.50	1.70	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =50mA	12.0	16.0		mW
Radiant Intensity	I _E	I _F =50mA		8		mW/sr
Peak Wavelength	λ _P	I _F =50mA	835	850	865	nm
Half Width	Δλ	I _F =50mA		40		nm
Viewing Half Angle	Q _{1/2}	I _F =50mA		±60		deg.
Rise Time	t _r	I _F =50mA		30		ns
Fall Time	t _f	I _F =50mA		25		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.

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